

# Abstracts

## Wide Band, Dual-Gate GaAs F.E.T. Output Limiters

*R.J. Hamilton, Jr.. "Wide Band, Dual-Gate GaAs F.E.T. Output Limiters." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 256-258.*

The use of dual-gate, GaAs FET devices as lower power output limiters in S- and X-Band is presented. Device characteristics, circuit design and advantages including a sharper saturation knee, small signal suppression, low loss and wide bandwidth performance are discussed.

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